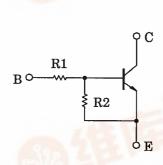
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

## RN1421,RN1422,RN1423,RN1424 RN1425,RN1426,RN1427

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

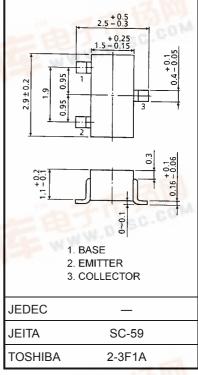
- High current type (I<sub>C</sub> (max) = 800mA)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Low VCE (sat)
- Complementary to RN2401~RN2406

#### **Equivalent Circuit and Bias Resister Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN1421	1	1
RN1422	2.2	2.2
RN1423	4.7	4.7
RN1424	10	10
RN1425	0.47	10
RN1426	1	10
RN1427	2.2	10

#### Unit: mm



Weight: 0.012 g (typ.)

### **Maximum Ratings (Ta = 25°C)**

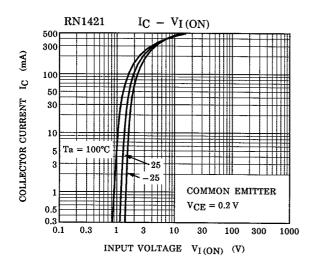
Characteris	Symbol	Rating	Unit		
Collector-base voltage	RN1421~1427	V <sub>CBO</sub>	50	V	
Collector-emitter voltage	- RN1421~1421	V <sub>CEO</sub>	50	V	
_ 1 HE 1 CE	RN1421~1424		10		
Emitter-base voltage	RN1425, 1426	V <sub>EBO</sub>	5	V	
	RN1427		6		
Collector current		IC	800	mA	
Collector power dissipation	RN1421~1427	PC	200	mW	
Junction temperature	- RN1421~1427	Tj	150	°C	
Storage temperature range	1	T <sub>stg</sub>	-55~150	°C	

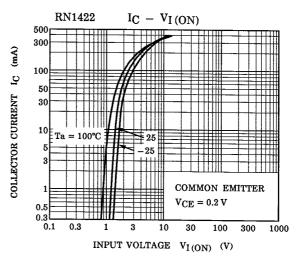


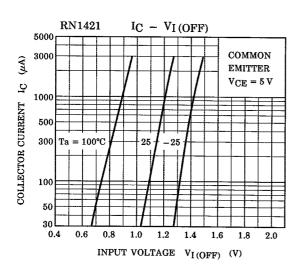
# **TOSHIBA**

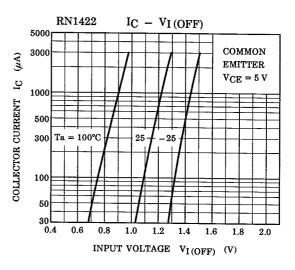
## Electrical Characteristics (Ta = 25°C)

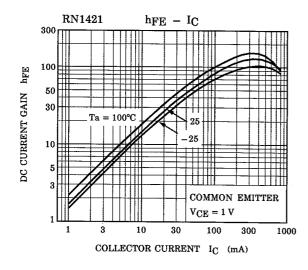
Characteri	istic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN1421~1427	I <sub>CBO</sub>		V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	_	_	100	nΛ
	KN 142 1~ 1421	I <sub>CEO</sub>		V <sub>CE</sub> = 50V, I <sub>B</sub> = 0	_	_	500	nA
Emitter cut-off current	RN1421	I <sub>EBO</sub>	_		3.85	_	7.14	mA
	RN1422			\/ = 40\/	1.75	_	3.25	
	RN1423			V <sub>EB</sub> = 10V, I <sub>C</sub> = 0	0.82	_	1.52	
	RN1424				0.38	_	0.71	
	RN1425			V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	0.365	_	0.682	
	RN1426				0.35	_	0.65	
	RN1427			V <sub>EB</sub> = 6V, I <sub>C</sub> = 0	0.378	_	0.703	
	RN1421				60	_	_	
	RN1422				65	_	_	
	RN1423				70	_	_	
DC current gain	RN1424	h <sub>FE</sub>	_	V <sub>CE</sub> = 1V, I <sub>C</sub> = 100mA	90	_	_	_
	RN1425	""			90	_	_	
	RN1426				90	_	_	
	RN1427				90	_	_	
Collector-emitter	DN1404-1407	V		I <sub>C</sub> = 50mA, I <sub>B</sub> = 2mA			0.25	\ /
saturation voltage	RN1421~1427	V <sub>CE</sub> (sat)	_	I <sub>C</sub> = 50mA, I <sub>B</sub> = 1mA	] _	_	0.25	V
	RN1421	V <sub>I</sub> (ON) -		V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 100mA	1.0	_	3.5	V
Input voltage (ON)	RN1422				1.4	_	4.5	
	RN1423				2.0	_	6.5	
	RN1424		_		3.0	_	12.0	
	RN1425				0.6	_	2.0	
	RN1426				0.7	_	2.5	
	RN1427				1.0	_	3.0	
	RN1421~1424	V <sub>I</sub> (OFF)	) –	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA	0.8	_	1.3	٧
Input voltage (OFF)	RN1425, 1426				0.4	_	0.8	
	RN1427				0.5		1.0	
Transition frequency	RN1421~1427	f <sub>T</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 20mA	_	300	_	MHz
Collector Output capacitance	RN1421~1427	C <sub>ob</sub>	_	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MH <sub>z</sub>	_	7	_	pF
	RN1421			_	0.7	1.0	1.3	kΩ
	RN1422				1.54	2.2	2.86	
	RN1423				3.29	4.7	6.11	
Input resistor	RN1424	R1	_		7	10	13	
	RN1425				0.329	0.47	0.61	
	RN1426				0.7	1.0	1.3	
	RN1427				1.54	2.2	2.86	
Resistor ratio	RN1421~1424				0.9	1.0	1.1	_
	RN1425	D1/D2			0.0423	0.047	0.0517	
	RN1426	R1/R2	_	_	0.09	0.1	0.11	
	RN1427				0.2	0.22	0.24	

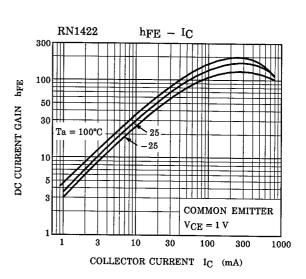




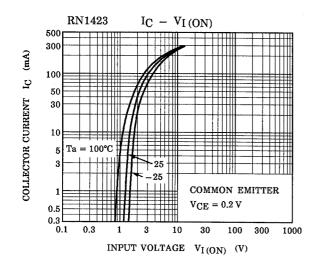


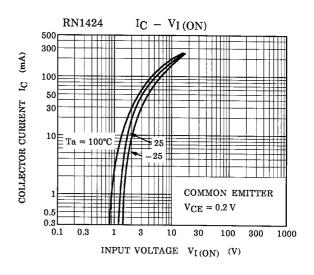


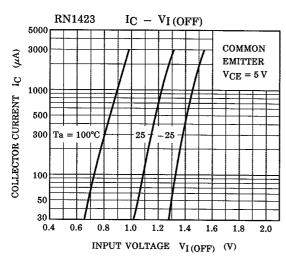


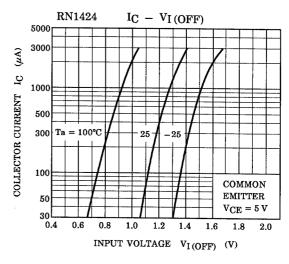


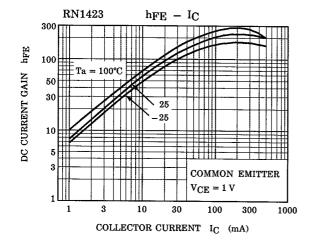
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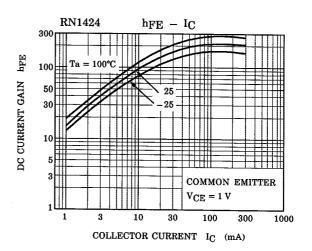




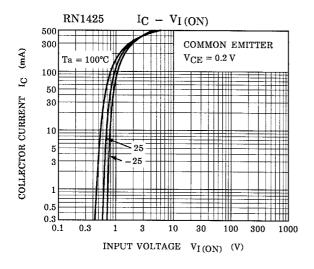


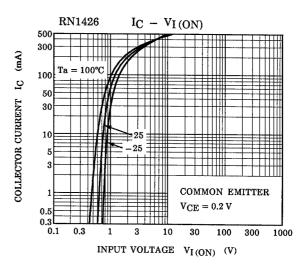


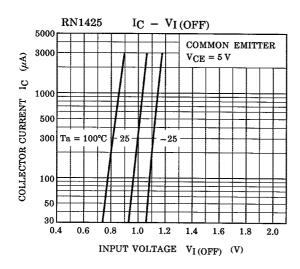


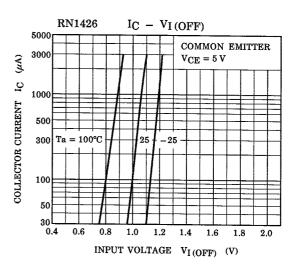


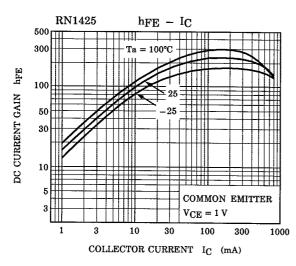
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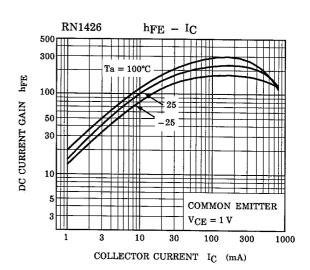




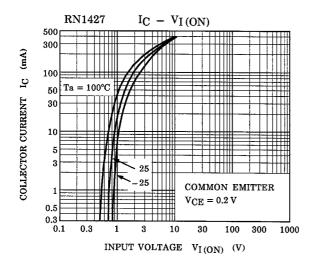


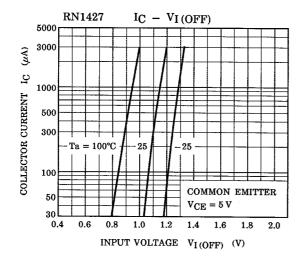


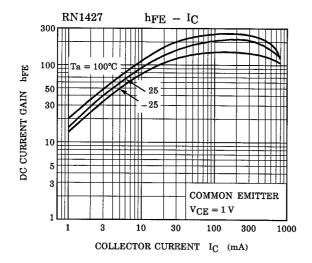




5







Type Name	Marking
RN1421	Type Name  Q A
RN1422	Type Name  Q B
RN1423	Type Name  Q C
RN1424	Type Name Q D
RN1425	Type Name Q E
RN1426	Type Name  Q F
RN1427	Type Name Q G

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